

20 V, 2 A NPN/NPN low VCEsat BISS double transistor

14 December 2015

Product data sheet

1. General description

NPN/NPN low V_{CEsat} Breakthrough In Small Signal (BISS) double transistor in a leadless medium power DFN2020D-6 (SOT1118D) Surface-Mounted Device (SMD) plastic package with visible and solderable side pads.

PNP/PNP complement: PBSS5220PAPS

2. Features and benefits

- Very low collector-emitter saturation voltage V_{CEsat}
- High collector current capability I_{C} and I_{CM}
- High collector current gain h_{FE} at high I_C
- Reduced Printed-Circuit Board (PCB) requirements
- Exposed heat sink for excellent thermal and electrical conductivity
- High energy efficiency due to less heat generation
- Suitable for Automatic Optical Inspection (AOI) of solder joints
- AEC-Q101 qualified

3. Applications

- Load switch
- Battery-driven devices
- Power management
- Charging circuits
- LED lighting
- Power switches (e.g. motors, fans)

4. Quick reference data

Table 1.	Quick reference data
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Symbol	Parameter	Conditions		Min	Тур	Мах	Unit
Per transistor							
V _{CEO}	collector-emitter voltage	open base		-	-	20	V
I _C	collector current			-	-	2	А
I _{CM}	peak collector current	single pulse; t _p ≤ 1 ms		-	-	3	А



20 V, 2 A NPN/NPN low VCEsat BISS double transistor

Symbol	Parameter	Conditions		Min	Тур	Max	Unit
Per transistor							
R _{CEsat}	collector-emitter saturation resistance	I_C = 1 A; I_B = 50 mA; pulsed; t_p ≤ 300 μs; δ ≤ 0.02 ; T_{amb} = 25 °C		-	-	170	mΩ

5. Pinning information

Table 2.	Pinning	information		
Pin	Symbol	Description	Simplified outline	Graphic symbol
1	E1	emitter TR1	6 5 4	C1 B2 E2
2	B1	base TR1		
3	C2	collector TR2	7 8	
4	E2	emitter TR2		
5	B2	base TR2	1 2 3	E1 B1 C2
6	C1	collector TR1	Transparent top view DFN2020D-6 (SOT1118D)	sym140
7	C1	collector TR1	DI 142020D-0 (SOTTIOD)	
8	C2	collector TR2		

6. Ordering information

Table 3. Ordering information					
Type number	Package				
	Name	Description	Version		
PBSS4220PANS	DFN2020D-6	DFN2020D-6: plastic, thermally enhanced ultra thin and small outline package; no leads; 6 terminals; body 2 x 2 x 0.65 mm	SOT1118D		

7. Marking

Table 4. Marking codes	
Type number	Marking code
PBSS4220PANS	3M

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8. Limiting values

Table 5. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions		Min	Мах	Unit
Per transis	tor		I			
V _{CBO}	collector-base voltage	open emitter		-	20	V
V _{CEO}	collector-emitter voltage	open base		-	20	V
V _{EBO}	emitter-base voltage	open collector		-	7	V
I _C	collector current			-	2	А
I _{CM}	peak collector current	single pulse; t _p ≤ 1 ms		-	3	А
I _B	base current			-	0.3	А
I _{BM}	peak base current	single pulse; t _p ≤ 1 ms		-	1	А
P _{tot} total power dissipation	total power dissipation	T _{amb} ≤ 25 °C	[1]	-	370	mW
			[2]	-	570	mW
			[3]	-	530	mW
			[4]	-	700	mW
Per device						_
P _{tot}	total power dissipation	T _{amb} ≤ 25 °C	[1]	-	510	mW
			[2]	-	780	mW
			[3]	-	730	mW
			[4]	-	960	mW
Tj	junction temperature			-	150	°C
T _{amb}	ambient temperature			-55	150	°C
T _{stg}	storage temperature			-65	150	°C

[1] Device mounted on an FR4 Printed-Circuit Board (PCB), single-sided copper, tin-plated and standard footprint.

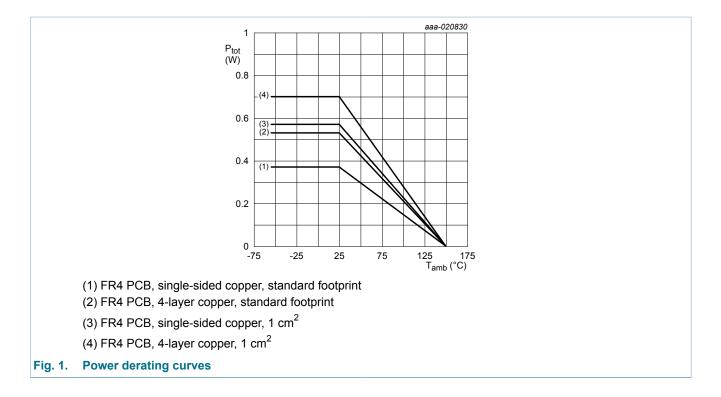
[2] Device mounted on an FR4 Printed-Circuit Board (PCB), single sided copper, tin-plated; mounting pad for collector 1 cm².

[3] Device mounted on an FR4 Printed-Circuit Board (PCB), 4-layer copper, tin-plated and standard footprint.

[4] Device mounted on an FR4 Printed-Circuit Board (PCB), 4-layer copper, tin-plated; mounting pad for collector 1 cm².

PBSS4220PANS

20 V, 2 A NPN/NPN low VCEsat BISS double transistor



9. Thermal characteristics

collector 1 cm².

Symbol	Parameter	Conditions		Min	Тур	Max	Unit
Per transist	or						
R _{th(j-a)}	thermal resistance	in free air	[1]	-	-	338	K/W
from junction to ambient		[2]	-	-	219	K/W	
	ambient		[3]	-	-	236	K/W
			[4]	-	-	179	K/W
Per device				1			
R _{th(j-a)}	thermal resistance	in free air	[1]	-	-	246	K/W
	from junction to ambient		[2]	-	-	161	K/W
	ambient		[3]	-	-	172	K/W
			[4]	-	-	131	K/W

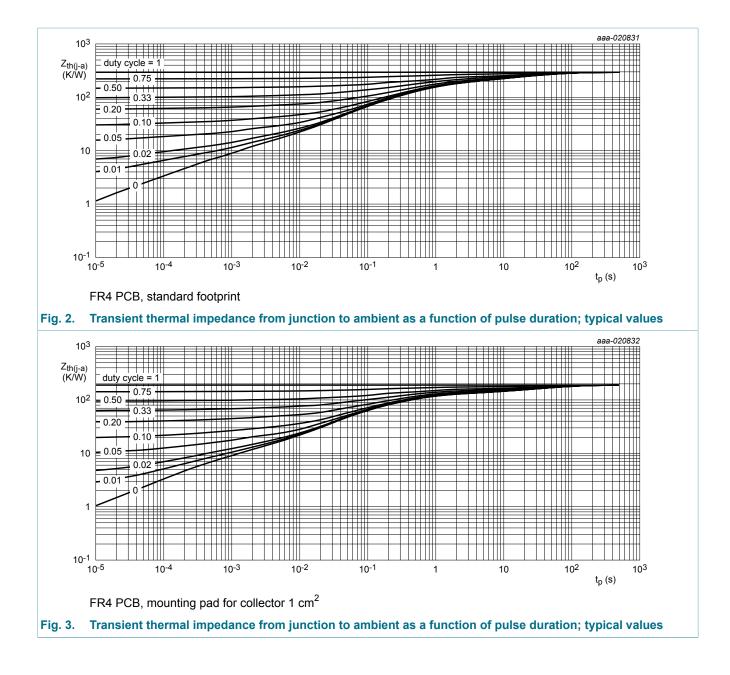
[1] Device mounted on an FR4 Printed-Circuit Board (PCB), single-sided copper, tin-plated and standard footprint.

[2] Device mounted on an FR4 Printed-Circuit Board (PCB), single-sided copper, tin-plated, mounting pad for collector 1 cm².

[3] Device mounted on an FR4 Printed-Circuit Board (PCB), 4-layer copper, tin-plated and standard footprint.
 [4] Device mounted on an FR4 Printed-Circuit Board (PCB), 4-layer copper, tin-plated, mounting pad for

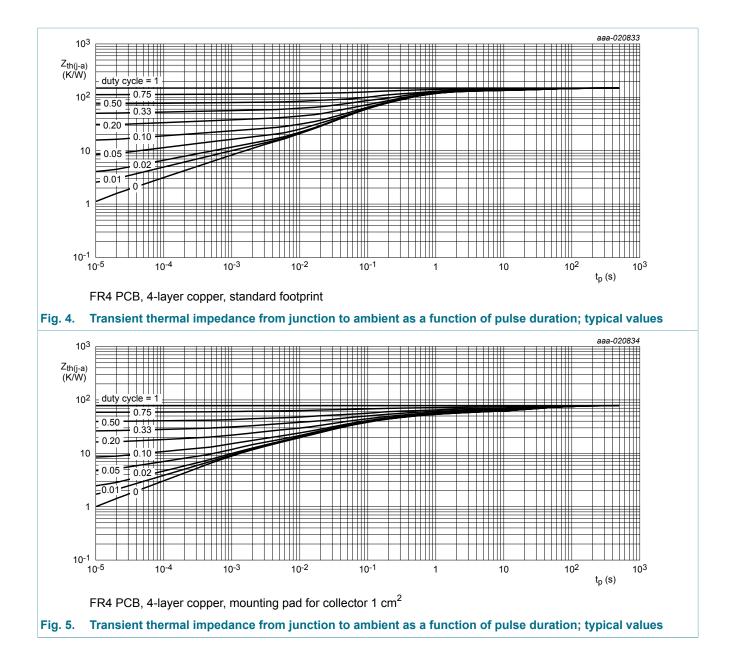
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20 V, 2 A NPN/NPN low VCEsat BISS double transistor



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20 V, 2 A NPN/NPN low VCEsat BISS double transistor



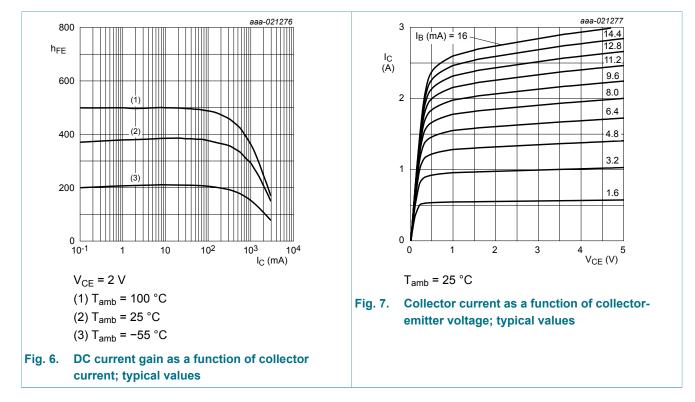
10. Characteristics

Symbol	Parameter	Conditions	Min	Тур	Мах	Unit
Per transis	tor					
current		V_{CB} = 16 V; I _E = 0 A; T _{amb} = 25 °C	-	-	100	nA
		V _{CB} = 16 V; I _E = 0 A; T _j = 150 °C	-	-	50	μA
I _{CES}	collector-emitter cut-off current	V_{CE} = 16 V; V_{BE} = 0 V; T_{amb} = 25 °C	-	-	100	nA
ЕВО	emitter-base cut-off current	V_{EB} = 5 V; I _C = 0 A; T _{amb} = 25 °C	-	-	100	nA
h _{FE}	DC current gain	$\begin{split} &V_{CE} = 2 \; V; \; I_{C} = 100 \; mA; \; pulsed; \\ &t_{p} \leq 300 \; \mus; \; \bar{o} \leq 0.02; \; T_{amb} = 25 \; ^{\circ}C \end{split}$	250	450	-	
		V_{CE} = 2 V; I _C = 500 mA; pulsed; t _p ≤ 300 µs; δ ≤ 0.02; T _{amb} = 25 °C	230	400	-	
		$\label{eq:Vce} \begin{split} V_{CE} &= 2 \; V; \; I_C = 1 \; A; \; \text{pulsed}; \; t_p \leq 300 \; \mu\text{s}; \\ \delta &\leq 0.02; \; T_{amb} = 25 \; ^\circ\text{C} \end{split}$	200	350	-	
		V_{CE} = 2 V; I_{C} = 2 A; pulsed; t_{p} \leq 300 $\mu s;$ δ \leq 0.02	150	260	-	
V _{CEsat}	collector-emitter saturation voltage	$\begin{split} I_C &= 0.5 \text{ A}; I_B = 50 \text{ mA}; \text{ pulsed}; \\ t_p &\leq 300 \mu\text{s}; \delta \leq 0.02 ; T_{\text{amb}} = 25 ^\circ\text{C} \end{split}$	-	60	90	mV
		I_C = 1 A; I_B = 50 mA; pulsed; $t_p \le 300 \ \mu$ s; δ ≤ 0.02 ; T_{amb} = 25 °C	-	125	170	mV
		$\begin{split} I_C &= 2 \text{ A}; I_B = 200 \text{ mA}; \text{ pulsed}; \\ t_p &\leq 300 \mu\text{s}; \delta &\leq 0.02 ; T_{\text{amb}} = 25 ^\circ\text{C} \end{split}$	-	240	320	mV
R _{CEsat}	collector-emitter saturation resistance	I_C = 1 A; I_B = 50 mA; pulsed; $t_p \le 300 \ \mu$ s; δ ≤ 0.02 ; T_{amb} = 25 °C	-	-	170	mΩ
V _{BEsat}	base-emitter saturation voltage	I_C = 0.5 A; I_B = 50 mA; pulsed; $t_p \le 300 \ \mu$ s; δ ≤ 0.02 ; T_{amb} = 25 °C	-	0.92	1	V
		I_{C} = 1 A; I_{B} = 50 mA; pulsed; t _p ≤ 300 μs; δ ≤ 0.02; T _{amb} = 25 °C	-	0.96	1.1	V
		I_C = 2 A; I_B = 200 mA; pulsed; $t_p \le 300 \ \mu$ s; δ ≤ 0.02 ; T_{amb} = 25 °C	-	1.18	1.3	V
V _{BE}	base-emitter voltage	$\begin{split} &I_{C} = 0.5 \text{ A}; \text{V}_{CE} = 2 \text{ V}; \text{ pulsed}; \\ &t_{p} \leq 300 \mu\text{s}; \delta_{factor} \leq 0.02; \text{T}_{amb} = 25 ^{\circ}\text{C} \end{split}$	-	0.77	0.9	V
t _d	delay time	I _C = 1 A; I _{Bon} = 50 mA; I _{Boff} = -50 mA;	-	10	-	ns
r	rise time	T _{amb} = 25 °C	-	50	-	ns
on	turn-on time		-	60	-	ns
ts	storage time		-	310	-	ns

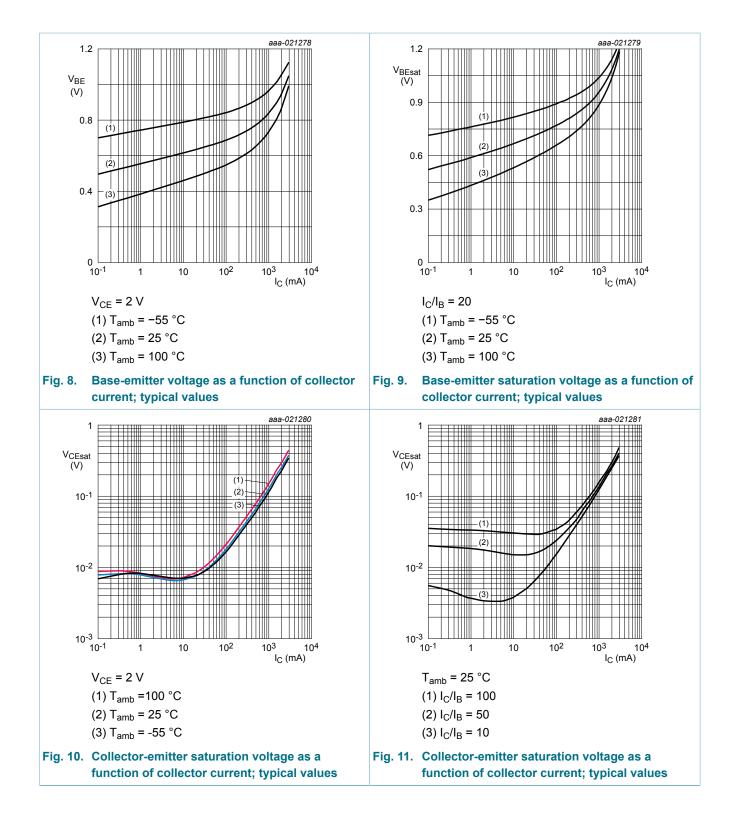
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Symbol	Parameter	Conditions	Min	Тур	Мах	Unit
t _f	fall time		-	60	-	ns
t _{off}	turn-off time		-	370	-	ns
f _T	transition frequency	V_{CE} = 10 V; I _C = 500 mA; f = 100 MHz; T _{amb} = 25 °C	-	120	-	MHz
C _c	collector capacitance	V _{CB} = 10 V; I _E = 0 A; i _e = 0 A; f = 1 MHz; T _{amb} = 25 °C	-	13.5	-	pF



20 V, 2 A NPN/NPN low VCEsat BISS double transistor

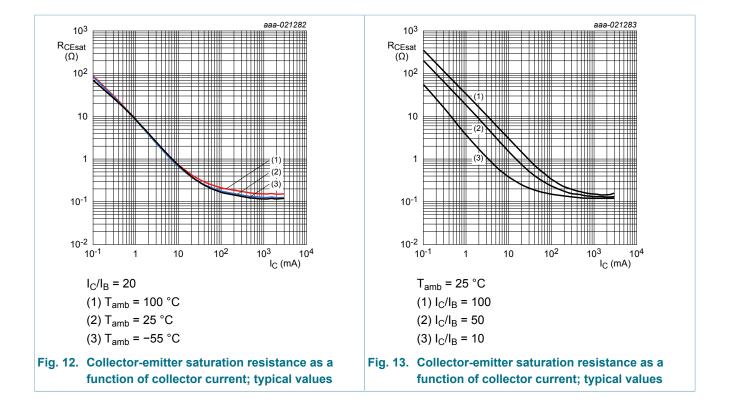


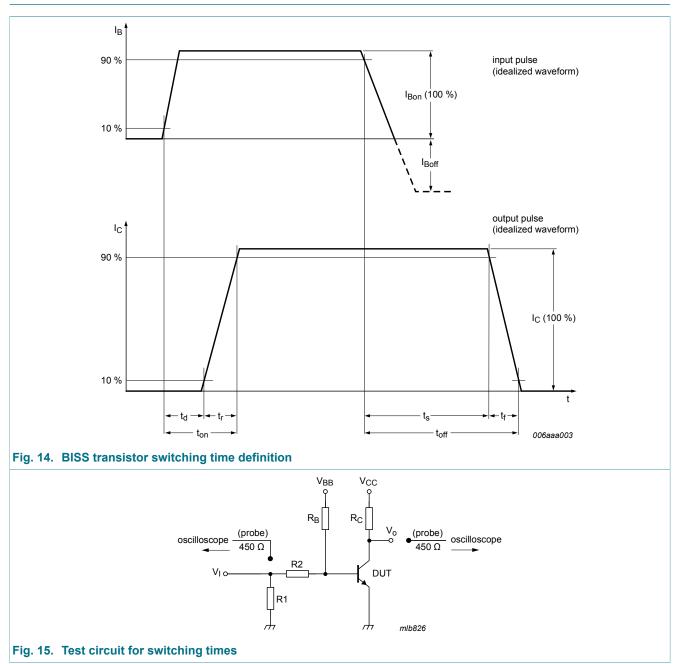
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11. Test information

11.1 Quality information

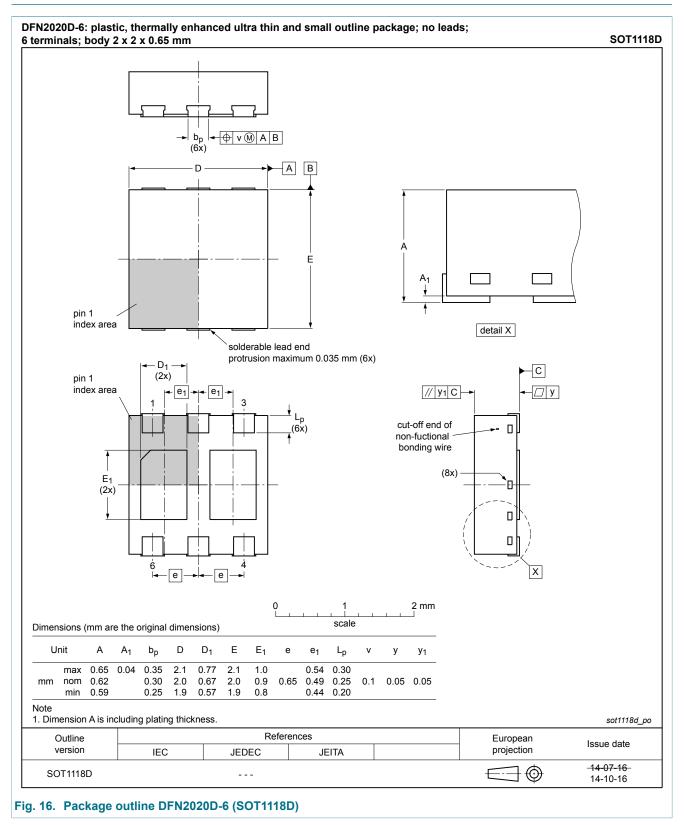
This product has been qualified in accordance with the Automotive Electronics Council (AEC) standard *Q101* - *Stress test qualification for discrete semiconductors*, and is suitable for use in automotive applications.

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12. Package outline



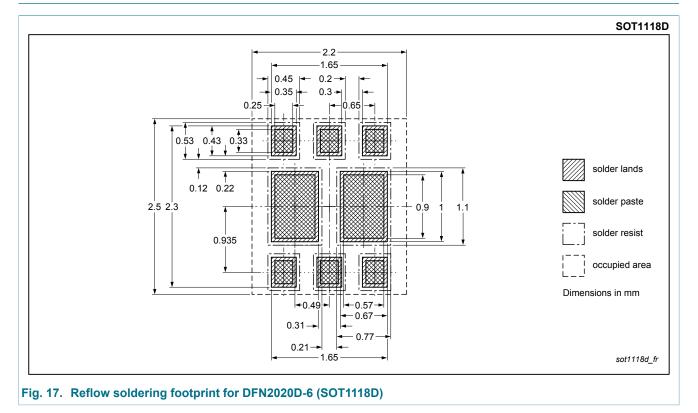
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13. Soldering



14. Revision history

Table 8. Revision his	able 8. Revision history					
Data sheet ID	Release date	Data sheet status	Change notice	Supersedes		
PBSS4220PANS v.1	20151214	Product data sheet	-	-		

20 V, 2 A NPN/NPN low VCEsat BISS double transistor

15. Legal information

15.1 Data sheet status

Document status [1][2]	Product status [<u>3]</u>	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

 Please consult the most recently issued document before initiating or completing a design.

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20 V, 2 A NPN/NPN low VCEsat BISS double transistor

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20 V, 2 A NPN/NPN low VCEsat BISS double transistor

16. Contents

1	General description	1
2	Features and benefits	1
3	Applications	1
4	Quick reference data	1
5	Pinning information	2
6	Ordering information	2
7	Marking	2
8	Limiting values	3
9	Thermal characteristics	4
10	Characteristics	7
11	Test information	11
11.1	Quality information	11
12	Package outline	12
13	Soldering	13
14	Revision history	14
15	Legal information	15
15.1	Data sheet status	15
15.2	Definitions	15
15.3	Disclaimers	15
15.4	Trademarks	16

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